IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Issue No.: 7,737,051
Issue Date: June 15, 2010
Serial No.: 10/797,876
Filing Date: March 10, 2004

Applicant: Dip et al.

Title: SILICON GERMANIUM SURFACE LAYER FOR HIGH-K

DIELECTRIC INTEGRATION

Attorney Docket: TPS-007 Confirmation No.: 5070

Cincinnati, Ohio 45202 August 27, 2010

VIA ELECTRONIC FILING

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

substrate--.

LETTER MAKING ERRORS OF RECORD

It is respectfully requested that this letter calling attention to the following errors in the specification in the above-identified patent be placed in the file wrapper history to make these errors of record.

In column 1, line 7, "processing, and more particularly," should read -- processing and, more particularly,--.

In column 7, line 32, "device be advantageous" should read -- device may be advantageous --. In column 9, line 3, Claim 18, "providing a Si_substrate" should read --providing a Si

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

By: /Kristi L. Davidson/

Kristi L. Davidson, Reg. No. 44,643

2700 Carew Tower 441 Vine Street Cincinnati, OH 45202 (513) 241-2324 (voice) (513) 241-6234 (facsimile) kdavidson@whepatent.com 1232381v1